

MOSFET – N-Channel, SUPERFET® II, FRFET®

600 V, 76 A, 41 mΩ

FCH041N60F

Description

SUPERFET II MOSFET is onsemi's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SUPERFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SUPERFET II FRFET MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.

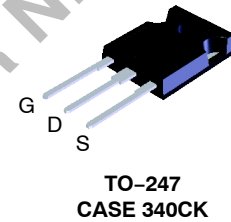
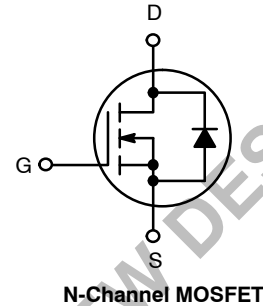
Features

- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 36\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 277\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 748\text{ pF}$)
- 100% Avalanche Tested
- This Device is Pb-Free, Halide Free, and is RoHS Compliant

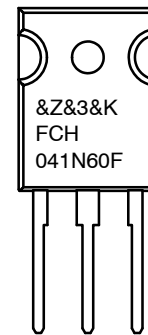
Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies
- EV Charger
- UPS / Solar

V_{DSS}	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	41 mΩ	76 A



MARKING DIAGRAM



&Z = Assembly Plant Code
 &3 = Data Code (Year & Week)
 &K = Lot Code
 FCH041N60F = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCH041N60F

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, Unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	DC	± 20
		AC ($f > 1\text{ Hz}$)	± 30
I_D	Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	76
		Continuous ($T_C = 100^\circ\text{C}$)	48.1
I_{DM}	Drain Current	Pulsed (Note 1)	228
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	2025	mJ
I_{AR}	Avalanche Current (Note 1)	15	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	5.95	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	50	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	595
		Derate Above 25°C	4.76
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. $I_{AS} = 15\text{ A}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.

3. $I_{SD} \leq 38\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq 380\text{ V}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.21	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH041N60F	FCH041N60F	TO-247	Tube	N/A	N/A	30 Units

FCH041N60F

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 10 mA, T _J = 25°C	600	–	–	V
		V _{GS} = 0 V, I _D = 10 mA, T _J = 150°C	650	–	–	
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	–	0.67	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	–	–	10	μA
		V _{DS} = 480 V, T _C = 125°C	–	267	–	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	3	–	5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 38 A	–	36	41	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 38 A	–	64.5	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	–	10800	14365	pF
C _{oss}	Output Capacitance		–	324	430	pF
C _{rss}	Reverse Transfer Capacitance		–	4.5	–	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	–	185	–	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	–	748	–	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 380 V, I _D = 38 A, V _{GS} = 10 V (Note 4)	–	277	360	nC
Q _{gs}	Gate to Source Gate Charge		–	65.3	–	nC
Q _{gd}	Gate to Drain "Miller" Charge		–	116	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	1.0	–	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 380 V, I _D = 38 A, V _{GS} = 10 V, R _G = 4.7 Ω (Note 4)	–	63	136	ns
t _r	Turn-On Rise Time		–	66	142	ns
t _{d(off)}	Turn-Off Delay Time		–	244	498	ns
t _f	Turn-Off Fall Time		–	53	116	ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I _S	Maximum Continuous Source to Drain Diode Forward Current	–	–	77	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	231	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 38 A	–	–	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 38 A, dI _F /dt = 100 A/μs	–	214	–	ns
Q _{rr}	Reverse Recovery Charge		–	1.79	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

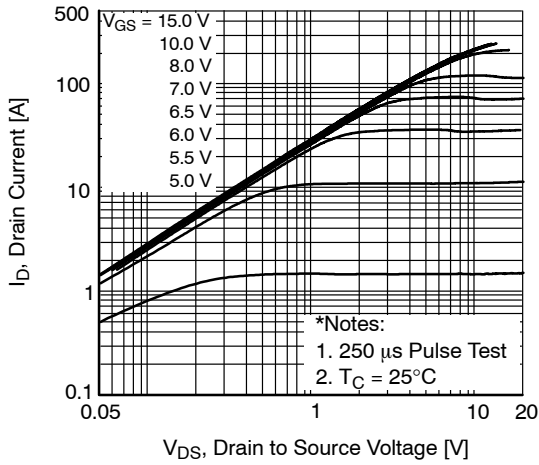


Figure 1. On-Region Characteristics

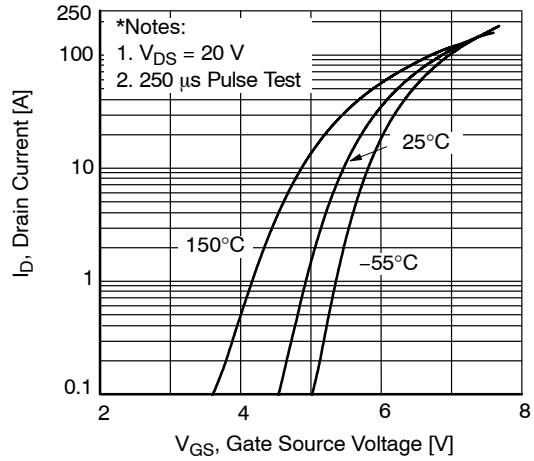


Figure 2. Transfer Characteristics

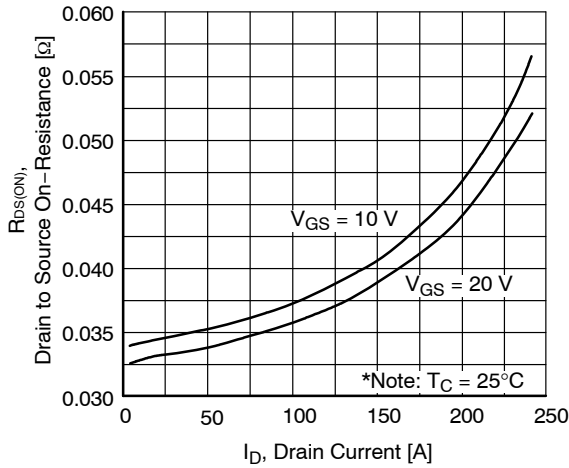


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

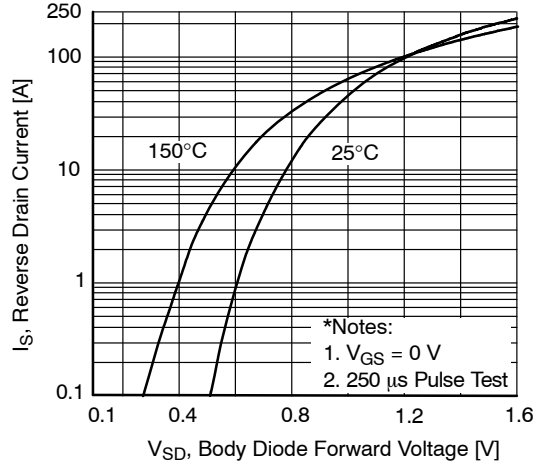


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

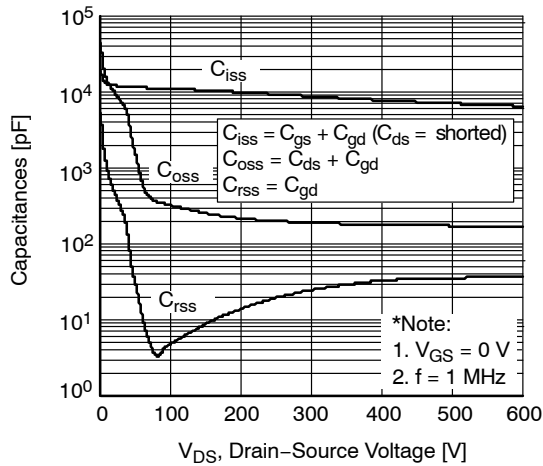


Figure 5. Capacitance Characteristics

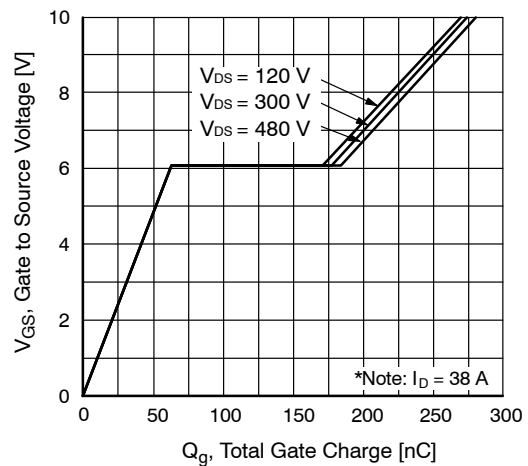


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

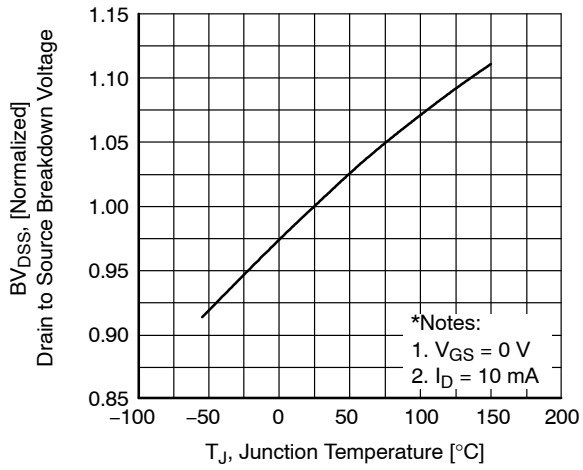


Figure 7. Breakdown Voltage Variation vs. Temperature

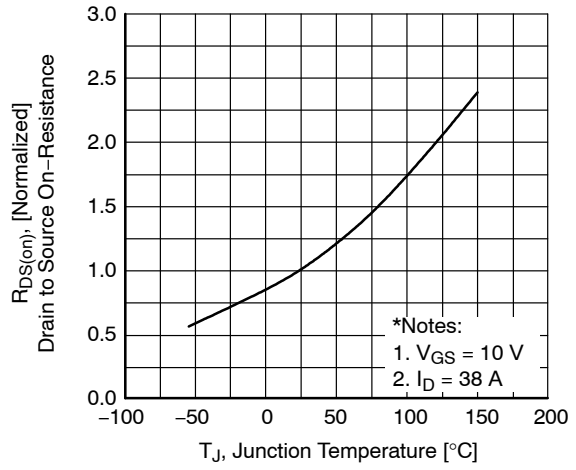


Figure 8. On-Resistance Variation vs. Temperature

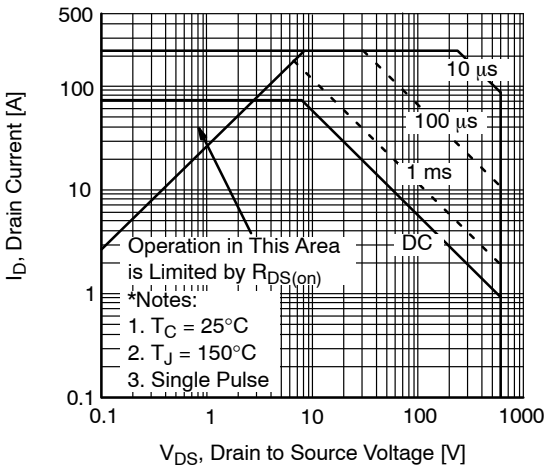


Figure 9. Maximum Safe Operation Area

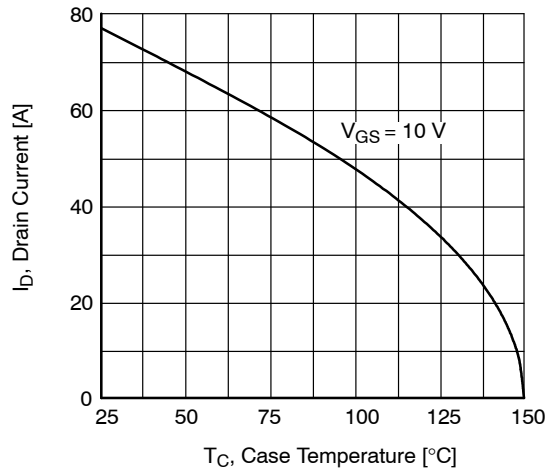


Figure 10. Maximum Drain Current vs. Case Temperature

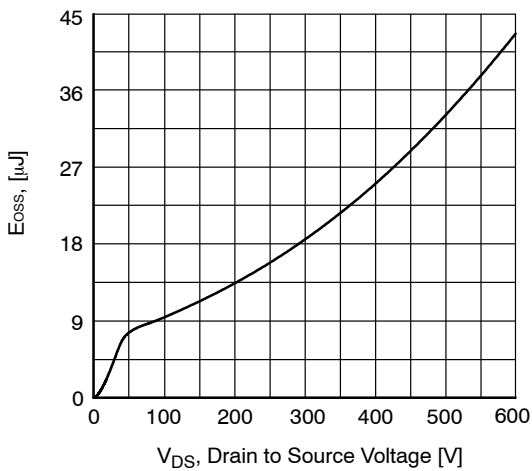


Figure 11. E_{OSS} vs. Drain to Source Voltage

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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

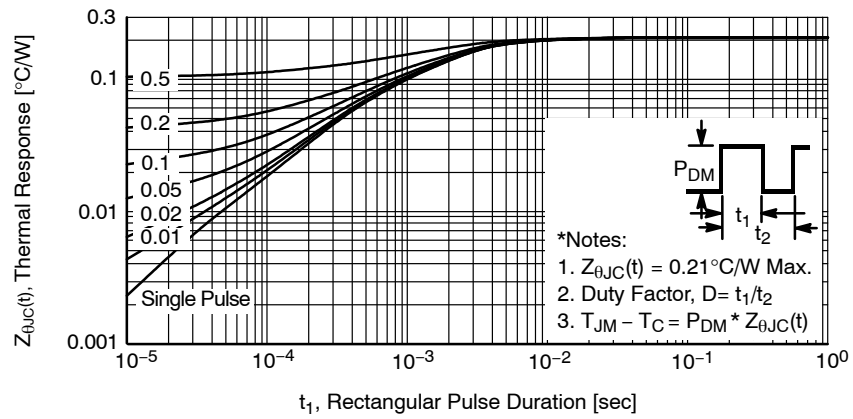


Figure 12. Transient Thermal Response Curve

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Figure 13. Gate Charge Test Circuit & Waveform

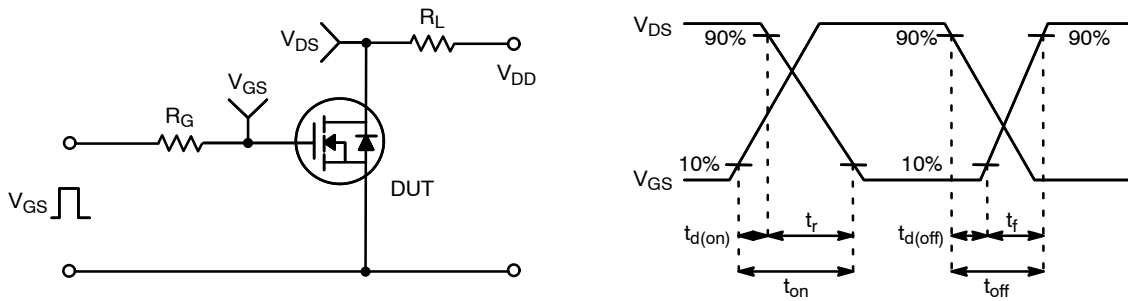


Figure 14. Resistive Switching Test Circuit & Waveforms

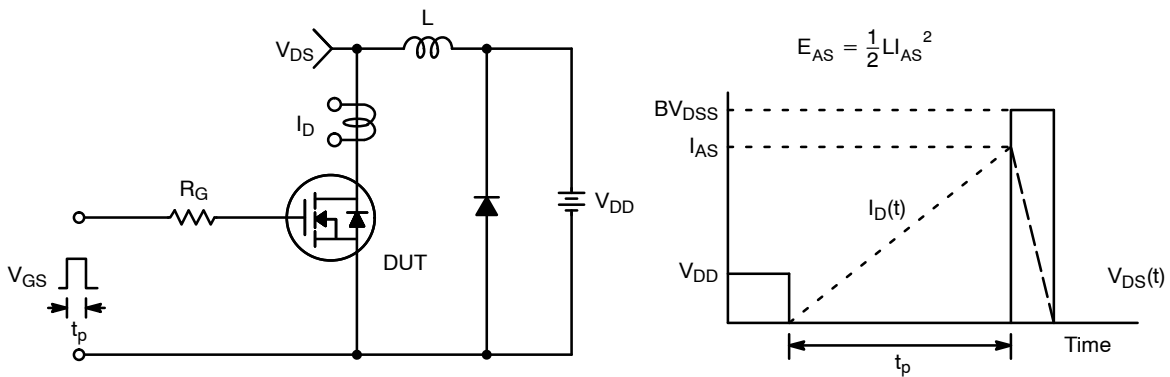


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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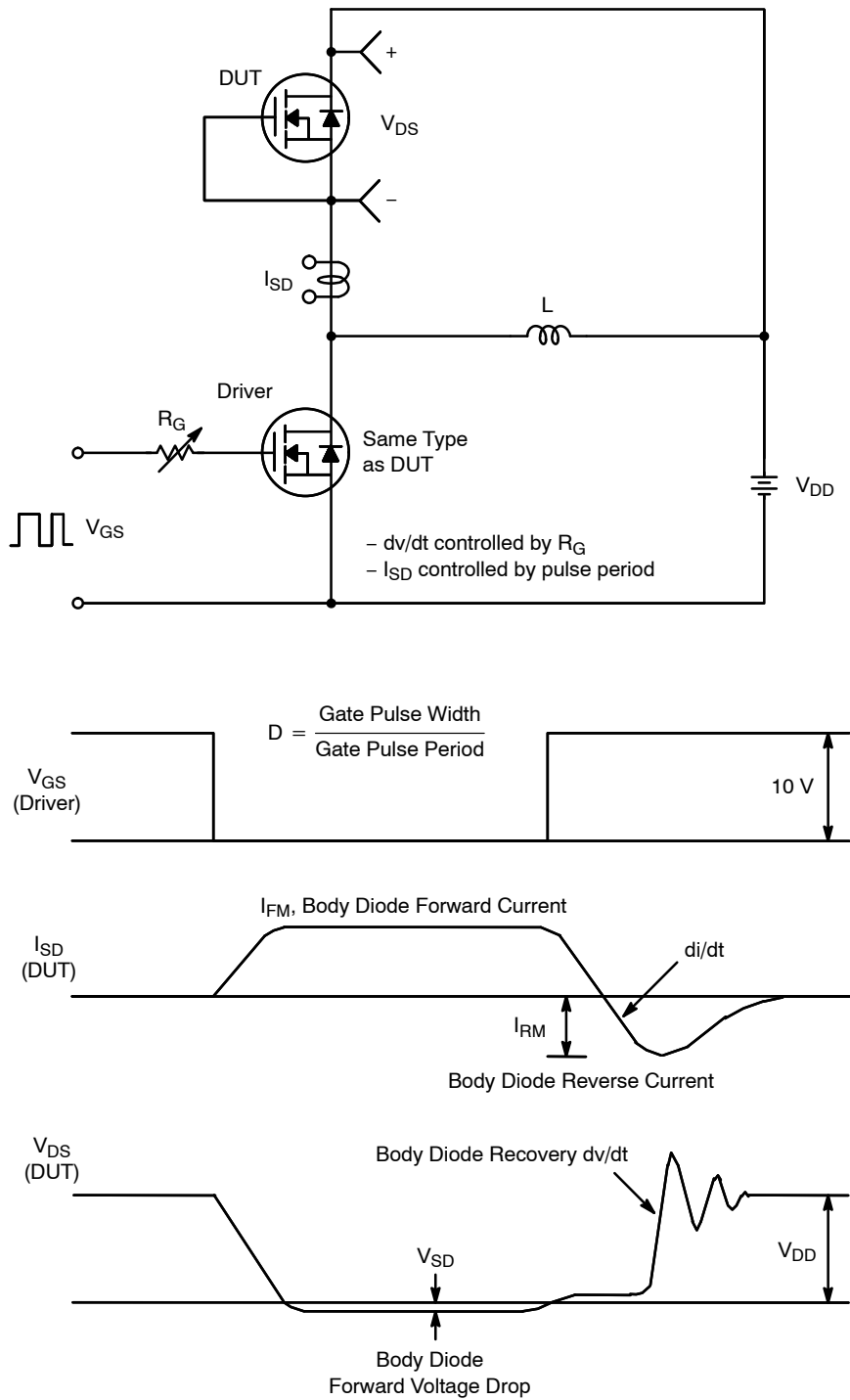


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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